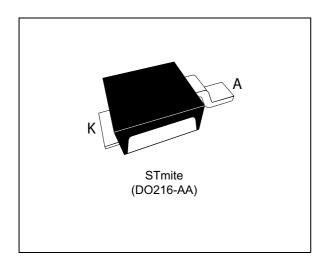
STPS120M



Power Schottky rectifier

Datasheet - production data



Features

- Very small conduction losses
- · Negligible switching losses
- Extremely fast switching
- Low forward voltage drop for higher efficiency and extented battery life
- Low thermal resistance
- · Avalanche capability specified

Description

Single Schottky rectifier suited for switch mode power supplies and high frequency DC to DC converters.

Packaged in STmite, this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications. Due to the small size of the package this device fits battery powered equipment (cellular, notebook, PDA's, printers) as well chargers and PCMCIA cards.

Table 1. Device summary

Symbol	Value
I _{F(AV)}	1 A
V _{RRM}	20 V
T _j (max)	150 °C
V _F (typ)	0.36 V

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1 Characteristics

Table 2. Absolute ratings (limiting values at T_{amb} = 25 °C, unless otherwise specified)

Symbol	Parameter			Unit
V_{RRM}	Repetitive peak reverse voltage	Repetitive peak reverse voltage		
I _{F(RMS)}	Forward rms current			Α
I _{F(AV)}	Average forward current, δ = 0.5, square wave T_c = 140 °C		1	Α
I _{FSM}	Surge non repetitive forward current	t _p = 8.3 ms sinusoidal	50	Α
P _{ARM} ⁽¹⁾	Repetitive peak avalanche power $T_j = 125 ^{\circ}\text{C}, t_p = 10 \mu\text{s}$		100	W
T _{stg}	Storage temperature range			°C
T _j	Maximum operating junction temperature ⁽²⁾			°C

For pulse time duration deratings, please refer to Figure 3. More details regarding the avalanche energy measurements and diode validation in the avalanche are provided in the STMicroelectronics Application notes AN1768, "Admissible avalanche power of Schottky diodes" and AN2025, "Converter improvement using Schottky rectifier avalanche specification".

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case	20	°C/W
R _{th(j-a)} ⁽¹⁾	Junction to ambient	250	°C/W

^{1.} Mounted with minimum recommended pad size, PC board FR4.

Table 4. Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
		T _j = 25 °C	V - V	-	1.3	3.9	4
		T _j = 100 °C	$V_R = V_{RRM}$	-	275	850	
I _R ⁽¹⁾	Boyoroo lookogo gurrant	T _j = 25 °C	V = 10 V	-	0.6	2.0	
I _R ⁽¹⁾ Reverse leakage current	T _j = 100 °C	V _R = 10 V	-	145	450	μA	
		T _j = 25 °C	V _R = 5 V	-	0.4	1.0	
		T _j = 100 °C		-	105	300	
		T _j = 25 °C	Ι – 1 Λ	-	0.44	0.49	
V _F ⁽¹⁾ Forward voltage drop	Forward voltage drap	T _j = 100 °C	I _F = 1 A	-	0.36	0.41	V
	T _j = 25 °C	1 - 2 4	-	0.48	0.54	V	
		T _j = 100 °C	I _F = 2 A	-	0.42	0.48	

^{1.} Pulse test: $t_p = 380 \mu s$, $\delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 0.34 \times I_{F(AV)} + 0.07 \times I_{F}^{2}_{(RMS)}$$



^{2.} $\frac{dPtot}{dT_j} < \frac{1}{Rth(j-a)}$ condition to avoid thermal runaway for a diode on its own heatsink

STPS120M Characteristics

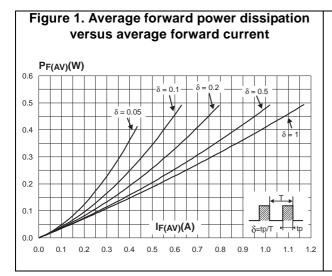
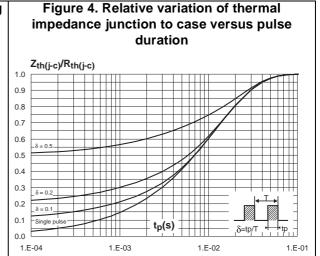
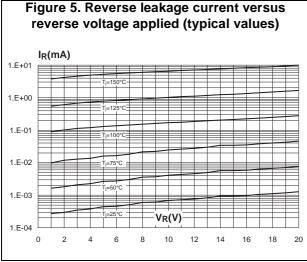
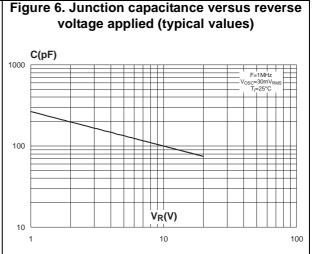


Figure 2. Average forward current versus ambient temperature ($\delta = 0.5$) $I_{\mathsf{F}(\mathsf{AV})}(\mathsf{A})$ 1.2 1.1 $R_{th(j-a)} = R_{th(j-c)}$ 1.0 0.9 0.8 0.7 0.6 0.5 0.3 0.2 0.1 δ= tp/T 0.0 0 25 50 100 125 150

Figure 3. Normalized avalanche power derating versus pulse duration (T_j = 125 °C)







Characteristics STPS120M

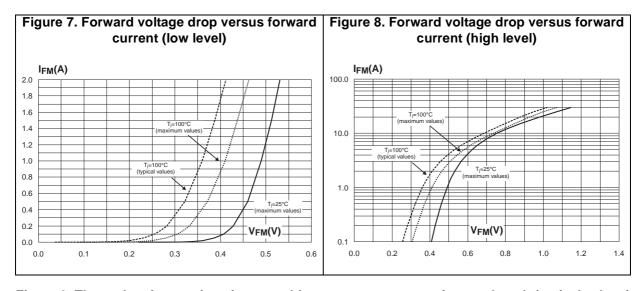
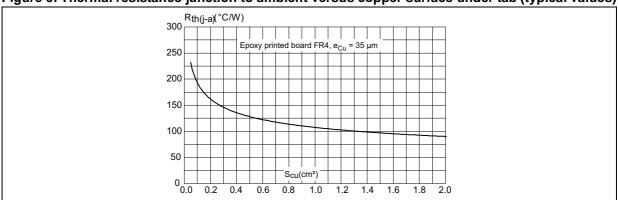


Figure 9. Thermal resistance junction to ambient versus copper surface under tab (typical values)



2 Package information

• Epoxy meets UL94, V0

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

2.1 STmite package information

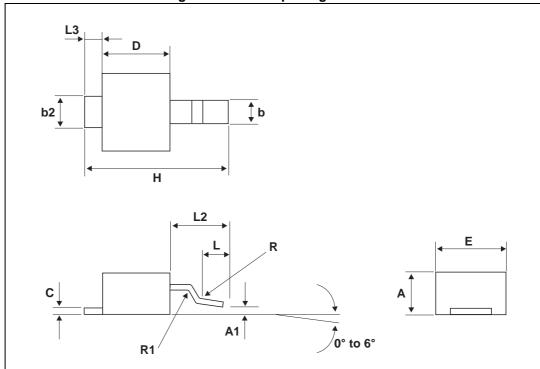


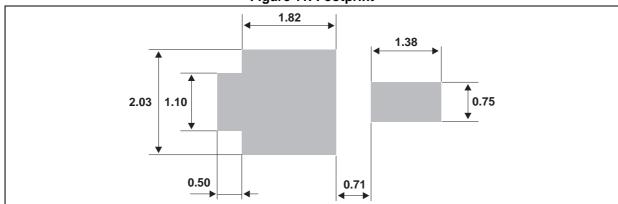
Figure 10. STmite package outline

Package information STPS120M

Table 5. STmite package mechanical data

	Dimensions					
Ref.	Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	0.85	1.00	1.15	0.033	0.039	0.045
A1	-0.05		0.05	-0.002		0.002
b	0.40		0.65	0.016		0.025
b2	0.70		1.00	0.027		0.039
С	0.10		0.25	0.004		0.010
D	1.75	1.90	2.05	0.069	0.007	0.081
Е	1.75	1.90	2.05	0.069	0.007	0.081
Н	3.60	3.75	3.90	0.142	0.148	0.154
L	0.50	0.63	0.80	0.020	0.025	0.031
L2	1.20	1.35	1.50	0.047	0.053	0.059
L3		0.50			0.019	
R	0.07			0.003		
R1	0.07			0.03		

Figure 11. Footprint



3 Ordering information

Table 6. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPS120M	120	STmite	15.5 mg	12000	Tape and reel

4 Revision history

Table 7. Document revision history

Date	Revision	Changes
Jul-2003	2A	Last update.
13-Sep-2004	3	STmite package dimensions reference A1 change: from blank (min) to -0.05mm and from 0.10 (max) to 0.05mm.
16-Feb-2011	4	Migrated from EDOCS.
20-Jul-2015	5	Updated Table 4 and reformatted to current standard.

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